WHAT IS CLAIMED IS:

A thin film patterning substrate, comprising:
a substrate;

banks, each of which includes an organic substance at least on its surface, said banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, each of said areas including an inorganic substance; and

a thin film arranged in at least one of said areas, the thin film being made from a fluid,

wherein said banks exhibit non-affinity for the fluid, said non-affinity being greater than that of said partitioned areas.

- 2. The thin film patterning substrate according to claim 1, wherein said inorganic substance is selected from a group consisting of an ITO, a glass and a crystal.
- 3. The thin film patterning substrate according to claim 1, wherein said organic substance includes polyimide.
- 4. The thin film patterning substrate according to claim 1, wherein said banks have heights of between about 1 μ m and about 2 μ m, while said thin film has a thickness between about 0.05 μ m and about 0.2 μ m.
- 5. The thin film patterning substrate according to claim 1, wherein the banks include a side surface and an upper surface both of which include said organic substance.
- 6. The thin film patterning substrate according to claim 1, wherein a contact angle of said fluid to the surface of said banks is about 50° or greater, while to the surface of said partitioned areas is about 30° or less.
- 7. The thin film patterning substrate according to claim 1, wherein said thin film includes a colored resin.

- 8. The thin film patterning substrate according to claim 1, wherein said thin film includes an organic semiconductor material.
- 9. The thin film patterning substrate according to claim 1, wherein said thin film is formed as a multi-layer structure.
- 10. The thin film patterning substrate according to claim 9, wherein said thin film includes at least one of a light emitting layer, a hole injection layer and an electron injection layer.
- 11. The thin film patterning substrate according to claim 1, further comprising a thin film transistor formed above said substrate.
 - 12. A thin film patterning substrate, comprising:

a substrate;

banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, said banks comprising a first layer including an inorganic substance and a second layer including an organic substance;

a thin film arranged in at least one of said areas, the thin film being made from a fluid, wherein said banks exhibit non-affinity for the fluid, said non-affinity being greater than that of said partitioned areas.

- 13. The thin film patterning substrate according to claim 12, wherein said first layer is disposed above said substrate and wherein said second layer is disposed above said first layer.
- 14. The thin film patterning substrate according to claim 12, wherein said first layer exhibits affinity for the fluid which is greater than that of said second layer.
- 15. The thin film patterning substrate according to claim 12, wherein a surface of said partitioned areas exhibits affinity for the fluid which is equal to or greater than that of said first layer.

- 16. The thin film patterning substrate according to claim 15, wherein the surface of said partitioned areas includes an inorganic substance.
- 17. The thin film patterning substrate according to claim 12, wherein a contact angle of said fluid to the surface of said first layer is between about 20° and about 50°, to the second layer is about 50° or greater, and to the surface of said partitioned areas is about 30° or less.
- 18. The thin film patterning substrate according to claim 12, wherein said first layer includes a material selected from a group consisting of a silicon oxide, a silicon nitride and an amorphous silicon.
- 19. The thin film patterning substrate according to claim 12, wherein said inorganic substance is selected from a group consisting of an ITO, a glass and a crystal.
- 20. The thin film patterning substrate according to claim 12, wherein said organic substance includes polyimide.
- 21. The thin film patterning substrate according to claim 12, wherein said banks have heights of between about 1 μm and about 2 μm , while said thin film has a thickness between about 0.05 μm and about 0.2 μm .
- 22. The thin film patterning substrate according to claim 12, wherein a thickness of said thin film is approximately equal to that of the first layer.
- 23. The thin film patterning substrate according to claim 12, wherein said thin film includes an organic semiconductor material.
- 24. The thin film patterning substrate according to claim 12, wherein said thin film includes a colored resin.
- 25. The thin film patterning substrate according to claim 12, further comprising a thin film transistor formed above said substrate.
 - 26. A thin film patterning substrate, comprising:

a substrate;

banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, said banks comprising a first layer and a second layer;

a thin film arranged in at least one of said areas, the thin film being made from a fluid, wherein a surface of said first layer exhibits affinity for the fluid which is greater than that of said second layer.

- 27. The thin film patterning substrate according to claim 26, wherein a surface of said partitioned areas exhibits affinity for the fluid that is equal to or greater than that of said first layer.
 - 28. An EL device comprising:

a substrate;

banks, each of which includes an organic substance at least on a surface, said banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, each of said areas including an inorganic substance; and

a semiconductor material being capable of emitting light and arranged in at least one of said areas, the semiconductor material being made from a fluid, wherein said banks exhibit non-affinity for the fluid, said non-affinity being greater than that of said partitioned areas.

- 29. The EL device according to claim 28, further comprising a plurality of semiconductor materials, each of which is capable of emitting light different in color and disposed in a respective one of the areas.
 - 30. An EL device comprising: a substrate;

banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, said banks comprising a first layer including an inorganic substance and a second layer including an organic substance;

a semiconductor material being capable of emitting light and arranged in at least one of said areas, the semiconductor material being made from a fluid, wherein said banks exhibit non-affinity for the fluid, said non-affinity being greater than that of said partitioned areas.

- 31. The EL device according to claim 30, further comprising a plurality of semiconductor materials, each of which is capable of emitting light different in color and disposed in a respective one of the areas.
 - 32. A thin film patterning substrate, comprising: a substrate;

banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, said banks comprising a first layer and a second layer;

a semiconductor material being capable of emitting light and arranged in at least one of said areas, the semiconductor material being made from a fluid,

wherein a surface of said first layer exhibits affinity for the fluid which is greater than that of said second layer.

- 33. The thin film patterning substrate according to claim 32, wherein a surface of said partitioned areas exhibits affinity for the fluid that is equal to or greater than that of said first layer.
- 34. The EL device according to claim 33, further comprising a plurality of semiconductor materials, each of which is capable of emitting light different in color and disposed in a respective one of the areas.